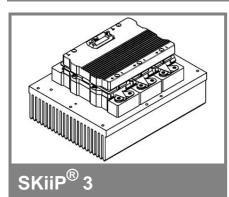
SKiiP 513GD172-3DUL



6-pack-integrated intelligent Power System

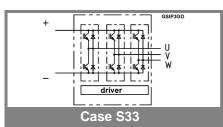
Power section

SKiiP 513GD172-3DUL

Data

Power section features

- SKiiP technology inside
- Trench IGBTs
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP[®] 3 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal



Absolute	• Maximum Ratings	$\Gamma_{s} = 25^{\circ}C$ unless otherwise specified				
Symbol	Conditions	Values	Units			
IGBT						
V _{CES}		1700	V			
V _{CC} ¹⁾	Operating DC link voltage	1200	V			
V _{GES}		± 20	V			
I _C	T _s = 25 (70) °C	500 (375)	А			
Inverse diode						
I _F = - I _C	T _s = 25 (70) °C	400 (300)	А			
I _{FSM}	T _j = 150 °C, t _p = 10 ms; sin	3500	А			
I²t (Diode)	Diode, T _j = 150 °C, 10 ms	61	kA²s			
T _j , (T _{stg})		- 40 + 150 (125)	°C			
V _{isol}	rms, AC, 1 min, main terminals to heat sink	4000	V			
I _{AC-terminal}	per AC terminal, rms, T _s = 70 °C,	400	А			
	T _{terminal} <115 °C					

Characteristics T _s = 25°C unless otherwise specif					specifie	
Symbol	Conditions	min.	typ.	max.	Units	
IGBT						
V _{CEsat}	I_{C} = 300 A, T_{j} = 25 (125) °C; measured at terminal		1,9 (2,2)	2,4	V	
V _{CEO}	T _i = 25 (125) °C; at terminal		1 (0,9)	1,2 (1,1)	V	
r _{CE}	T _i = 25 (125) °C; at terminal		3 (4,1)	3,9 (5)	mΩ	
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} , T _i = 25 (125) °C		1,2 (72)		mA	
E _{on} + E _{off}	$I_{\rm C}^{\rm J}$ = 300 A, $V_{\rm CC}$ = 900 V		195		mJ	
	T _j = 125 °C, V _{CC} = 1200 V		288		mJ	
R _{CC+EE} '	terminal chip, T _i = 25 °C		0,5		mΩ	
L _{CE}	top, bottom		12		nH	
C _{CHC}	per phase, AC-side		1,7		nF	
Inverse	diode					
V _F = V _{EC}	$I_F = 300 \text{ A}, T_j = 25 (125) ^{\circ}\text{C}$ measured at terminal		1,9 (1,7)	2,4	V	
V _{TO}	T _i = 25 (125) °C		1,1 (0,8)	1,4 (1,1)	V	
r _T	T _j = 25 (125) °C T _j = 25 (125) °C		2,6 (2,9)	3,4 (3,7)	mΩ	
Err	I _C = 300 A, V _{CC} = 900 V		36		mJ	
	T _j = 125 °C, V _{CC} = 1200 V		43		mJ	
Mechan	ical data					
M _{dc}	DC terminals, SI Units	6		8	Nm	
M _{ac}	AC terminals, SI Units	13		15	Nm	
W	SKiiP [®] 3 System w/o heat sink		2,4		kg	
w	heat sink		7,5		kg	
Thermal characteristics (PX 16 heat sink with fan SKF16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc.IEC 60747-15)						
R _{th(i-s)I}	per IGBT	I		0,059	K/W	
R _{th(j-s)D}	per diode			0,115	K/W	
Z _{th}	R _i (mK/W) (max. values)	1	tau	i(s)	1	
		1 4	•			

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee, expressed or implied is made regarding delivery, performance or suitability.

4

0

60

1,4

1

363

30

210

3

21

54

5,5

2

28,8

36

20

2

0,18

5

85

3

0,04

0,25

11

4

1

0,04

0,4

1

10,2

36

2,1

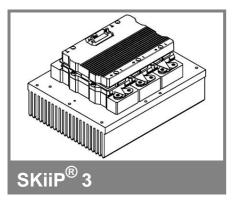
Z_{th(j-r)I}

Z_{th(j-r)D}

Z_{th(r-a)}

1

SKiiP 513GD172-3DUL



6-pack-integrated intelligent Power System

6-pack integrated gate driver SKiiP 513GD172-3DUL

Data

Gate driver features

- CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- Interlock of top/bottom switch
- Isolation by transformer
- IEC 60068-1 (climate) 40/85/56
- UL recognized file no. 242581

Absolute	Maximum Ratings	T _a = 25°C unless otherwise specified		
Symbol	Conditions	Values	Units	
V _{S2}	unstabilized 24 V power supply	30	V	
V _i	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/µs	
V _{isolIO}	input / output (AC, rms, 2s)	4000	V	
VisoIPD	partial discharge extinction voltage, rms, $Q_{PD} \leq 10 \text{ pC}$;	1500	V	
V _{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V	
f _{sw}	switching frequency	14	kHz	
f _{out}	output frequency for I _{peak(1)} =I _C	14	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

Characteristics (T _a			= 25°C)		
Symbol	Conditions	min.	typ.	max.	Units
V _{S2}	supply voltage non stabilized	13	24	30	V
I _{S2}	V _{S2} = 24 V	420+34*f/l	Hz+0,000′	15*(I _{AC} /A) ²	mA
V _{iT+}	input threshold voltage (High)			12,3	V
V _{iT-}	input threshold voltage (Low)	4,6			V
R _{IN}	input resistance		10		kΩ
C _{IN}	input capacitance		1		nF
t _{d(on)IO}	input-output turn-on propagation time		1,3		μs
t _{d(off)IO}	input-output turn-off propagation time		1,3		μs
t _{pERRRESET}	error memory reset time		9		μs
t _{TD}	top / bottom switch interlock time		3		μs
I _{analogOUT}	max. 5mA; 8 V corresponds to 15 V supply voltage for external components		500		A
I _{s1out}	max. load current			50	mA
I _{TRIPSC}	over current trip level (I _{analog} OUT = 10 V)		625		A
T _{tp} U _{DCTRIP}	over temperature protection U _{DC} -protection (U _{analog OUT} = 9 V); ()	110	1200	120	°C V

For electrical and thermal design support please use SEMISEL. Access to SEMISEL is via SEMIKRON website http://www.semikron.com.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee, expressed or implied is made regarding delivery, performance or suitability.

